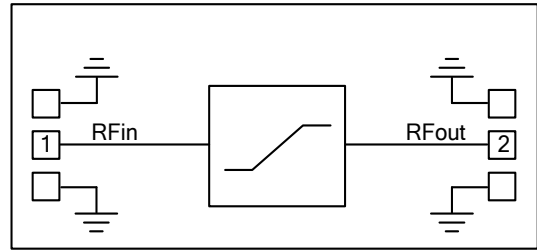


Feature

- Frequency : 10GHz~18GHz
- Insertion Loss: 0.6dB
- VSWRin/out: 1.5/1.5
- Limiting Level: 17.5dBm
- Peak Power: 20W(pluse 100us, duty cycle 20%)
- Diemsnion : 2.00mm×1.20mm×0.10mm

Function Diagram



Microwave electrical specification (T_A = +25°C)

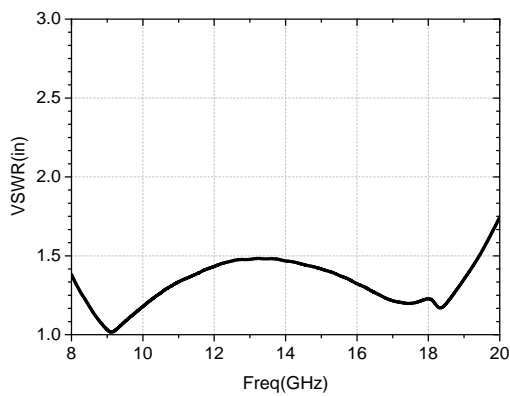
Parameter	Symbol	Min	Typical	Max	Unit
Frequency	f	10~18			GHz
Insertion Loss	IL		0.6	0.9	dB
VSWRin/out	VSWR		1.5	1.8	-
Limiting Level	P _{Lim}		17.5		dBm
Peak Power	P _p	20			W

Max Limited Values

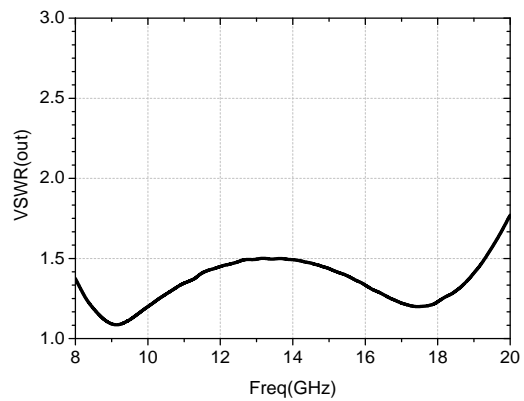
Parameter	Symbol	Values
Max Pin	P _p	20W
Storage Temperature	T _{STG}	-65°C~+150°C
Operation Temperature	T _{op}	-55°C~+125°C

Testing Curves

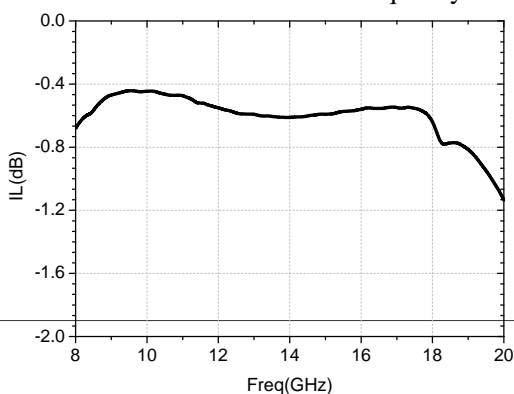
VSWRin vs. Frequency



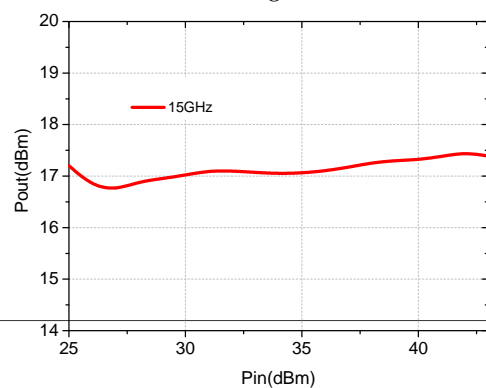
VSWRout vs. Frequency



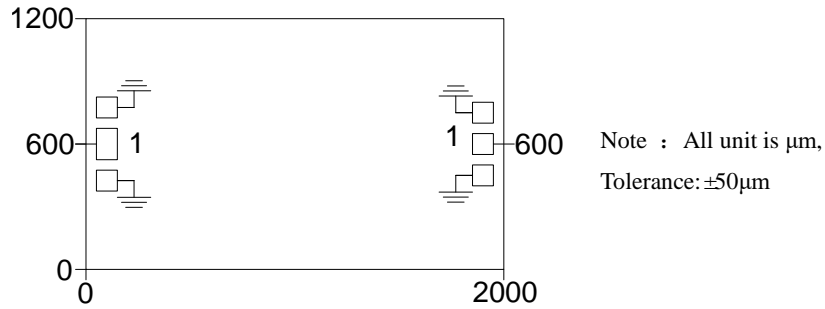
Insertion Loss vs. Frequency



Limiting Level



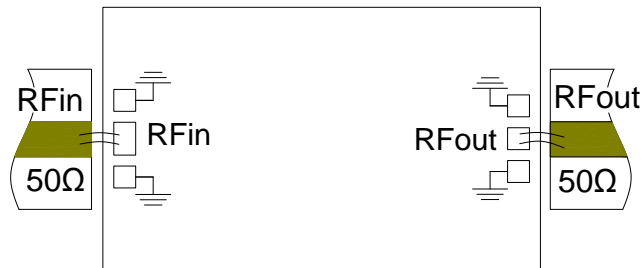
Outline and Dimension



Pad Definition

No	Symbol	Function	PAD dimension
1	RFin	RF Signal input pad	150×100μm ²
2	RFout	RF Signal output pad	100×100μm ²

Assembly Diagram



Attention

- 1) Assembly and use in a clean environment;
- 2) The GaAs material is very brittle, the surface of the chip is easily damaged (do not touch the surface), and care must be taken when using it;
- 3) Two bonding wires (25 μm diameter gold wire) for input and output, and about 300 μm bonding wire;
- 4) The input and output terminals have a DC blocking capacitor;
- 5) The back of the chip must be grounded;
- 6) Sintered with 80/20 gold tin, the sintering temperature should not exceed 300 °C, the sintering time should be as short as possible, not more than 30 seconds;
- 7) This product is a static sensitive device, pay attention to anti-static when storing and using;
- 8) Dry and nitrogen storage;
- 9) Do not attempt to clean the surface of the chip by dry or wet chemical methods;
- 10) If you have any questions, please contact the supplier.